

**AMENDMENTS TO THE SPECIFICATION**

Please replace the paragraph appearing at page 1, between lines 19 and 24 of the original specification with the following amended paragraph:

Recently, film thickness reduction of an active layer (less than 0.10  $\mu\text{m}$  ~~or thinner~~) has been progressed in conjunction with a highly densified integration of devices. There has been developed the smart cut method as a method for manufacturing a semiconductor substrate having an SOI (Silicon On Insulator) structure for achieving the above-mentioned film thickness reduction.

Please replace the paragraph bridging pages 2 and 3 of the original specification with the following amended paragraph:

Further, in recent years, the film thickness has been reduced as thin as less than 0.10  $\mu\text{m}$  ~~or thinner~~ (e.g., 0.02  $\mu\text{m}$  to 0.05  $\mu\text{m}$ ) for the active layer and 0.15  $\mu\text{m}$  for the buried silicon oxide film. Owing to this, the LPD (Light Point Defect) evaluation for measuring a surface defect (such as COP) of the active layer with a particle counter has a fear that a micro void could be detected as a pseudo defect. The term, micro void, refers to a minute gap present between the silicon oxide film and the supporting wafer (such as the COP emerging in a bonding interface of the supporting wafer). Such a detection of the micro void as the pseudo defect is due to the fact that a laser light used for the measurement can pass through the active layer of thin film and the

buried silicon oxide film. As a result, the reliability of the LPD evaluation has been made low.

Please replace the paragraph appearing at page 11, between lines 1 and 3 of the original specification with the following amended paragraph:

A third invention provides a manufacturing method of an SOI wafer as defined in the first invention, in which a thickness of the SOI layer is less than 0.10  $\mu\text{m}$  or ~~thinner~~.

Please replace the paragraph appearing at page 11, between lines 4 and 6 of the original specification with the following amended paragraph:

A fourth invention provides a manufacturing method of an SOI wafer as defined in the second invention, in which a thickness of the SOI layer is less than 0.10  $\mu\text{m}$  or ~~thinner~~.

Please replace the paragraph appearing at page 11, between lines 8 and 15 of the original specification with the following amended paragraph:

According to the third and the fourth inventions, even if the active layer and the buried silicon oxide film are processed to have their film thickness reduced to such a

thickness of SOI layer as thin as less than 0.10  $\mu\text{m}$  ~~or thinner~~ that allows a laser light for the LPD evaluation to pass through the layer and the film, respectively, the LPD evaluation never detects the micro void existing between the buried insulating film and the supporting wafer as the pseudo defect. Consequently, the reliability of the LPD evaluation of the active layer can be enhanced.

Please replace the paragraph appearing at page 13, between lines 13 and 23 of the original specification with the following amended paragraph:

A tenth invention provides an SOI wafer manufactured by a method comprising the steps of:

bonding a wafer for active layer with a supporting wafer via an insulating film interposed therebetween to thereby form a bonded wafer; and then

reducing a film thickness in a part of the active layer wafer of the bonded wafer to thereby form an SOI layer for manufacturing the SOI wafer, wherein

the supporting wafer that has been bonded contains boron by an amount of  $9 \times 10^{18}$  atoms/cm<sup>3</sup> or more, and the SOI layer has a thickness of less than 0.10  $\mu\text{m}$  ~~or thinner~~.